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| Substitute for Form 1449 A & B/PTO <u>INFORMATION DISCLOSURE</u> <u>STATEMENT BY APPLICANT</u> <i>(use as many sheets as necessary)</i> | | | | <i>Complete if Known</i> | |
| | | | | Application Number | 10/510,916 |
| | | | | Confirmation Number | 7320 |
| | | | | Filing Date | October 12, 2004 |
| | | | | First Named Inventor | Shinichi ISHIBASHI |
| | | | | Art Unit | 2812 |
| Sheet 1 of 1 | | | | Examiner Name | Not yet assigned |
| | | | | Attorney Docket Number | Q84137 |

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| Examiner Initials ^a | Cite No. ¹ | Document Number | | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document |
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| NON PATENT LITERATURE DOCUMENTS | | | |
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| Examiner Initials ^a | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published. | Translation ⁶ |
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| Examiner Signature | | Date Considered | |
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